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Contents

GaN-based electronics M. Kuzuhara	1
Early stage degradation of InAlN/GaN HEMTs during electrical stress M. Ľapajna, D. Gregušová, K. Čičo, J. Fedor, J.-F. Carlin, N. Grandjean, N. Killat M. Kuball, and J. Kuzmík	7
TCAD modeling of current dispersion in a 0.25 μm gate length GaN HEMT S. Faramehr, P. Igič, and K. Kalna	11
Investigation of robust bandgap semiconductor structures using optical spectroscopy methods J. Kováč jr, J. Kováč, R. Srnánek, and I. Novotný	15
Conductive metal oxide based gates for self-aligned technology of AlGaIn/GaN HEMTs G. Vanko, M. Vallo, I. Rýger, J. Dzuba, and T. Lalinský	19
Gates of AlGaIn/GaN HEMT for High Temperature Gas Sensing Applications I. Rýger, G. Vanko, P. Kunzo, T. Lalinský, J. Dzuba, M. Vallo, L. Satrapinsky, T. Plecenik, and A. Chvála	23
High temperature AlGaIn/GaN HFET microwave characterization M. Tomáška	27
Characterization and control of insulated gates for GaN power switching transistors T. Hashizume	31
Current instabilities and other reliability aspects in AlGaIn/GaN MOS-HFETs with atomic layer deposited Al_2O_3 as gate oxide R. Stoklas, D. Gregušová, J. Novák, P. Kordoš, M. Tajima, and T. Hashizume	37
Influence of layer structure on electrical properties of AlGaIn/GaN HEMTs P. Benko, J. Kováč, A. Chvála, M. Florovič, P. Kordoš, J. Škriniarová, and L. Harmatha	41
Material and device issues of InAlN/GaN heterostructures J. Kuzmík	45
Electrical characterization of the InAlN/GaN heterostructures by capacitance methods Ľ. Stuchlíková, M. Petrus, J. Kováč, J. Rybár, L. Harmatha, D. Donoval, J. Benkovská, H. Behmenburg, and M. Heuken	51
Electrothermal analysis of $\text{In}_{0.12}\text{Al}_{0.88}\text{N}/\text{GaN}$ HEMTs M. Molnár, G. Donnarumma, V. Palankovski, J. Kuzmík, D. Donoval, J. Kováč, and S. Selberherr	55
Interface traps in insulator/AlGaIn/GaN heterostructure capacitors J. Osvald	59
Arsenide-based Terahertz materials and devices for 800 and 1550 nm excitations M. Missous, I. Kostakis, and D. Saeedkia	63
GaAs nanowhiskers for femtosecond photodetectors and THz emitters M. Mikulics, J. Zhang, R. Sobolewski, R. Adam, L. Juul, M. Marso, A. Winden, H. Hardtdegen, D. Grützmacher, and P. Kordoš	71
Improving output power of terahertz heterodyne photomixer by impedance matching L. Juul, M. Mikulics, and M. Marso	75
Cathodoluminescence characterization of InGaIn/GaN QW pyramidal structure by Monte Carlo method J. Priesol and A. Šatka	79

Nanostructures for plasmonic solar cells and biosensing L. Wu	83
Nucleation and annihilation of magnetic vortices in Pacman-like nanodots observed by micro-Hall probes M. Precner, D. Gregušová, J. Šoltýs, J. Fedor, F. Guemann, J. Tóbič, R. Kúdela, and V. Cambeli	87
Detection elements for on-cantilever laboratory T. Ščepka, D. Gregušová, Š. Gaži, Š. Haščík, J. Fedor, J. Šoltýs, R. Kúdela and V. Cambel	91
Numerical simulation study of barrier inhomogeneities at Schottky contacts Subhash Chand and Priyanka Kaushal	95
Fabrication of 250-nm T-gate In₅₂Al₄₈As-In₇₀Ga₃₀As pHEMT using a novel solvent reflow technique at room temperature K. W. Ian, M.A. Exarchos, and M. Missous	99
Deep levels in InGaAsN/GaAs and InGaAs/GaAs heterojunctions J. Rybár, Ľ. Stuchlíková, M. Petrus, L. Harmatha, B. Ščiana, D. Radziewicz, D. Pucicki, and M. Tłaczała	103
The influence of an AlO_x film in-situ deposited on the GaAs-based HFETs properties D. Gregušová, R. Kúdela, R. Stoklas, M. Blaho, F. Guemann, J. Fedor, and P. Kordoš	107
Devices with Te-doped InGaP layers R. Kúdela, D. Gregušová, and R. Stoklas	111
Electrical characterisation of a-Si:H(n)/c-Si(p) heterostructures for solar cell applications M. Míkolášek, M. Nemeč, J. Kováč, G. Mannino, C. Gerardi, C. Tringali, L. Harmatha, and S. Lombardo	115
GaP/ZnO nanowires with a radial pn heterojunction A. Dujavová-Laurenčíková, I. Novotný, J. Kováč, P. Eliáš, S. Hasenöhrl, and J. Novák	119
Influence of the MOVPE growth parameters on the properties of InGaAsN/GaAs MQW structures for solar cells application D. Radziewicz, B. Ščiana, D. Pucicki, J. Serafińczuk, M. Tłaczała, M. Latkowska, M. Florovič, and J. Kováč	123
Photoluminescence of single GaP/ZnO core-shell nanowires J. Novák, M. Mikulics, P. Eliáš, S. Hasenöhrl, A. Dujavová-Laurenčíková, I. Vávra, I. Novotný, and J. Kováč	127
Graphene based FETs F. Schwierz	131
The d-dotFET: MosFET based on locally strained silicon J. Gerharz, J. Moers, G. Mussler, and D. Grützmacher	139
Metal/SI GaAs/Metal systems: Demonstration of unpinning of the Fermi level at the interface F. Dubecký, P. Hubík, E. Gombia, D. Kindl, M. Dubecký, J. Mudroň, P. Boháček, and M. Sekáčová	143
Influence of active volume on detection efficiency of GaAs neutron detectors A. Šagátová, B. Zaťko, K. Sedláčková, F. Dubecký, P. Boháček, and V. Nečas	147
Detector of fast neutrons based on silicon carbide epitaxial layers B. Zaťko, F. Dubecký, A. Šagátová, K. Sedláčková, P. Boháček, M. Sekáčová, and V. Nečas	151
Optical and electrical characterization of photonic crystal light emitting diodes P. Hronec, J. Kováč jr., J. Škriniarová, J. Kováč, and Ľ. Šušlík	155

Investigation of MQW GaInNAs/GaAs p-i-n photodetector Hagir. M. Khalil, N. Balkan, and S. Mazzucato	159
Low temperature investigation of electrical and optical properties of InGaAsN/Gas QW Schottky barrier photodetectors M. Florovič, J. Kováč, B. Šciana, D. Radziewicz, D. Pucicki, I. Zborowska-Lindert, M. Tlaczala, and I. Vávra	163
2D irregular structure patterning and analysis of LED by NSOM D. Pudis, I. Kubicova, J. Skriniarova, J. Kovac, J. Jakabovic, J. Novak, L. Suslik, and S. Hascik	167
Properties of Al₂O₃ thin films grown by atomic layer deposition K. Fröhlich, M. Mičušík, E. Dobročka, P. Šiffalovič, F. Guemann, and J. Fedor	171
Gas sensing properties and electrical resistance of Langmuir-Blodgett iron oxide nanoparticle arrays Š. Luby, P. Šiffalovič, M. Benkovičová, E. Majková, M. Jergel, J. Ivančo, R. Rella, M. G. Manera	175
2/3-D circuit electro-thermal model of power MOSFET for SPICE-like simulation A. Chvála, D. Donoval, J. Marek, P. Pribytný, and M. Molnár	179
Degradation of the low voltage power MOSFET electrical parameters during multipulse UIS test J. Marek, D. Donoval, M. Petrus, L. Stuchlíková, A. Chvála, M. Molnár, and P. Pribitný	183
DC Characterization of InGaAs/InAlAs/InP based pseudomorphic HEMT (pHEMT) M. Ahmad, H.T.Butt, T. Tauqeer, and M. Missous	187
Towards future III-nitride based THz OEICs in the UV range A. Fox, M. Mikulics, A. Winden, H. Hardtdegen, D. Gregušová, R. Adam, R. Sobolewski, M. Marso, D. Grützmacher, and P. Kordoš	191
THz generation and detection using ultrafast, high resistivity III-V semiconductor photoconductors at 1.55 μm pulse excitation I. Kostakis, D. Saeedkia, and M. Missous	195
Relaxation of low-frequency noise in AlGaIn/GaN HEMTs A. Šatka, K. Rendek and J. Priesol	199
Development of diffusion barriers for Ti/Al based ohmic contact to AlGaIn/GaN heterostructures W. Macherzynski and B. Paskiewicz	203
The impact of changed barrier layer parameters upon tunnelling in GaN/AlGaIn/GaN Schottky structures J. Racko, M. Mikolášek, R. Granzner, N. Al Mustafa, F. Schwier, and J. Breza	207
Characteristics of GaN MOSFET with stacked gate dielectric of MgO and TiO₂ G. Dutta	211
Thermal stability of IrO₂ gate based AlGaIn/GaN HEMT M. Vallo, T. Lalinský, G. Vanko, I. Rýger, J. Dzuba, and M. Držík	215
Experimental set-up for on-chip characterization of electronic devices by time domain reflectometry L. Sládek, A. Šatka, M. Bernát, D. Donoval, and J. Kováč	219
Tuning the spectral sensitivity of vertical InN nanopyramid based photodetectors by means of band gap engineering and/or nanostructure size control St. Trellenkamp, M. Mikulics, A. Winden, R. Adam, J. Moers, M. Marso, D. Grützmacher, and H. Hardtdegen	223
Distribution of fixed oxide charge in MOS structures with ALD grown Al₂O₃ studied by capacitance measurements L. Válik, M. Ťapajna, F. Guemann, J. Fedor, P. Šiffalovič, and K. Frohlich	227

Photoreflectance study of the role of a thin AlO_x layer in a GaAs surface passivation and the Schottky barrier forming	231
M. Kučera, R. Kúdela, and J. Novák	
Strain accommodation within porous buffer layers in heteroepitaxial growth	235
J. Grym, D. Nohavica, P. Gladkov, J. Vaniš, E. Hulicius, J. Pangrác, O. Pacherová, and K. Piksová	
Electrical characterization of GaSb buried p-n junction	239
M. Baldini, E. Gombia, A. Parisini, L. Tarricone, C. Ghezzi, C. Frigeri, and A. Gasparotto	
Tunnel junction technology for multijunction solar cell applications	243
B. Ściana, I. Zborowska-Lindert, D. Radziejwicz, D. Pucicki, M. Panek, J. Jureńczyk, W. Dawidowski, M. Badura, and M. Tłaczala	
Surface barrier 4H-SiC soft X-ray detector for hot plasmas diagnostic	247
F. Dubecký, E. Gombia, G. Vanko, C. Ferrari, B. Zaťko, P. Kováč, D. Baček, M. Baldini, L. Ryć, and V. Nečas	
Hydrogen silsesquioxane as a gate dielectric layer for SiC graphene FET T	251
J. Náhlík, M. Janoušek, Z. Šobáň, J. Voves, V. Jurka, and P. Macháč	
Application of single-crystal CVD diamond and SiC detectors for diagnostics of ion emission from laser plasmas	255
L. Ryć, L. Calcagno, F. Dubecký, D. Margarone, T. Nowak, P. Parys, M. Pfeifer, F. Riesz, and L. Torrisi	
Laser Ablation: A supporting technique to micromachining of SiC	259
G. Vanko, J. Zehenter, P. Choleva, T. Lalinský, and P. Hudek	
Photocathode based on deuterated diamond like carbon films prepared by reactive magnetron sputtering and PECVD technology	263
J. Huran, N.I. Balalykin, M. Kadlečiková, B. Zaťko, A.A. Feschenko, A.P. Kobzev, L. Vančo, M.A. Nozdrin, A. Kleinová, and E. Kováčova	
Electron cyclotron resonance plasma technology of silicon carbon nitride thin films	267
J. Huran, M. Kučera, P. Boháček, A.P. Kobzev, A. Kleinová, M. Sekáčová, and E. Kováčova	
Surface potential measurements of a single ZnO nanofiber	271
A. Stafiniak, A. Szyszka, J. Prażmowska, B. Boratynski, A. Baranowska-Korczyc, K. Fronc, D. Elbaum, and M. Tłaczala	
An influence of oblique-angle sputtering on ZnO:Ga thin film properties	275
S. Flickyngerová, M. Netřvalová, P. Šutta, I. Novotný, and V. Tvarožek	
Photocurrents in double-layer organic field-effect transistors	279
J. Jakabovič, M. Weis, J. Kováč, D. Donoval, M. Donoval, J. Círák, Y. Peng, J. Xie, W. Lv, T. Yang, B. Yao, and Y. Wang	
Electrical properties of 2,6-bis(5'-hexyl-2,2'-bithiophene-5-yl) naphthalene organic transistors: Effect of preparation conditions	283
M. Weis, J. Jakabovič, D. Donoval, J. Filo, and M. Putala	
Estimation of exposure parameters of chosen e-beam resists using variable shaped e-beam pattern generator	287
R. Andok, L. Matay, I. Kostič, A. Benčurová, P. Nemeč, A. Konečnicková, and A. Ritomský	
Sputtered NiO thin films for organic vapours testing	291
M. Predanocy, I. Hotový, M. Čaplovičová, V. Řeháček, I. Košč, and L. Spiess	
Influence of Ga addition on structure, thermal and magnetic properties of CoFeBSiNb metallic glasses	295
J. Hosko, I. Janotova, P. Svec, I. Matko, D. Janickovic, and P. Svec Sr.	
Emission and absorption properties of patterned LED with 2D PhC	299
L. Suslik, D. Pudis, J. Skrinjarova, J. Kovac, J. Kovac jr., I. Kubicova, J. Novak, S. Hascik	

Design, simulation and evaluation of AWG based demultiplexers	303
D. Seyringer, F. Uherek, J. Chovan, and A. Kuzma	
Deposition and properties of ZnO thin films on GaP nanowires	307
D. Búc, J. Kováč, M. Čaplovičová, T. Brath, S. Hasenöhrl, and J. Novák	
Bistable System for Energy Harvesting	311
M. Majer and M. Husak	
Acoustic Wave Sensor System Design Consideration	315
A. Laposá, M. Majer, and M. Husak	
Author index	319